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Kim et al.

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(54) **SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME**

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See application file for complete search history.

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Primary Examiner — Whitney T Moore

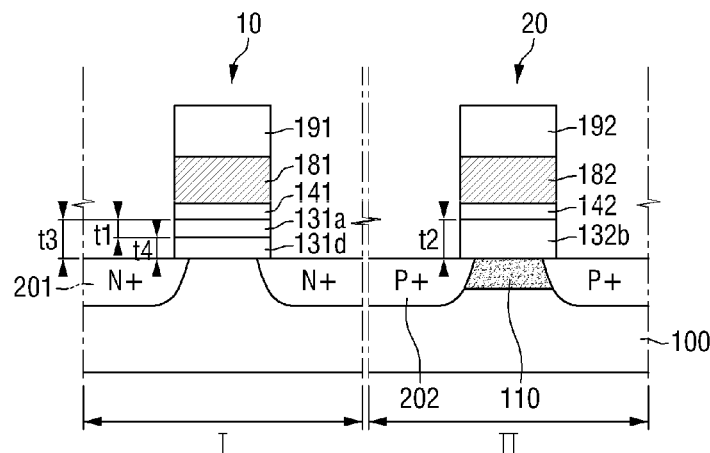
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(57) **ABSTRACT**

A semiconductor device includes a first interface film on a first area of a substrate, the first interface film including a first growth interface film and a second growth interface film on a lower portion of the first growth interface film, a first dielectric film on the first interface film, and a first gate electrode on the first dielectric film.

8 Claims, 7 Drawing Sheets

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FIG. 1

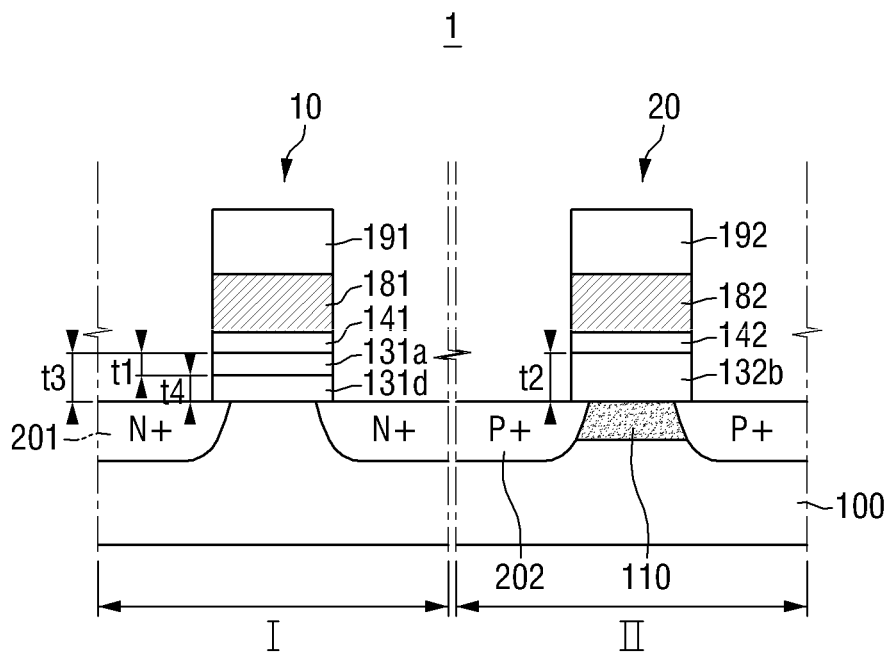


FIG. 2

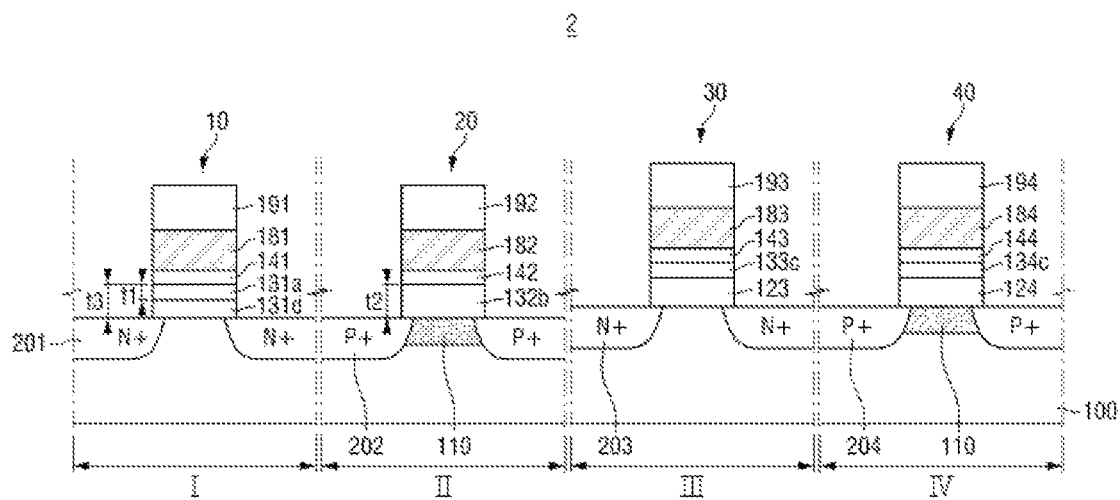


FIG. 3

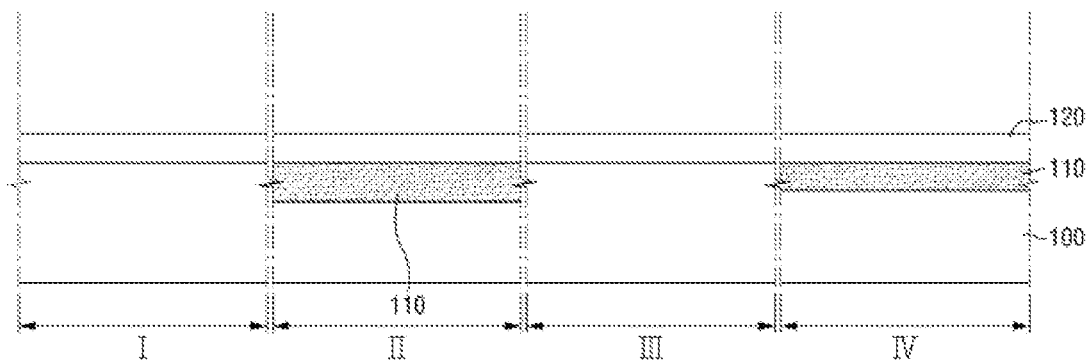


FIG. 4

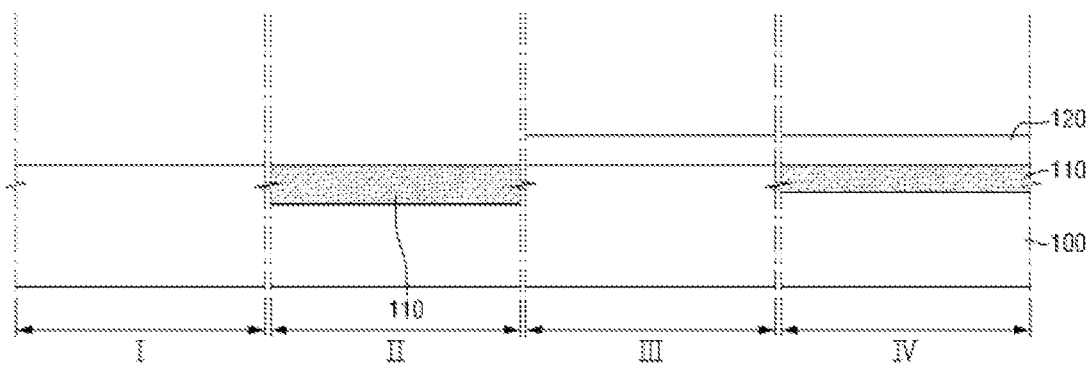


FIG. 5

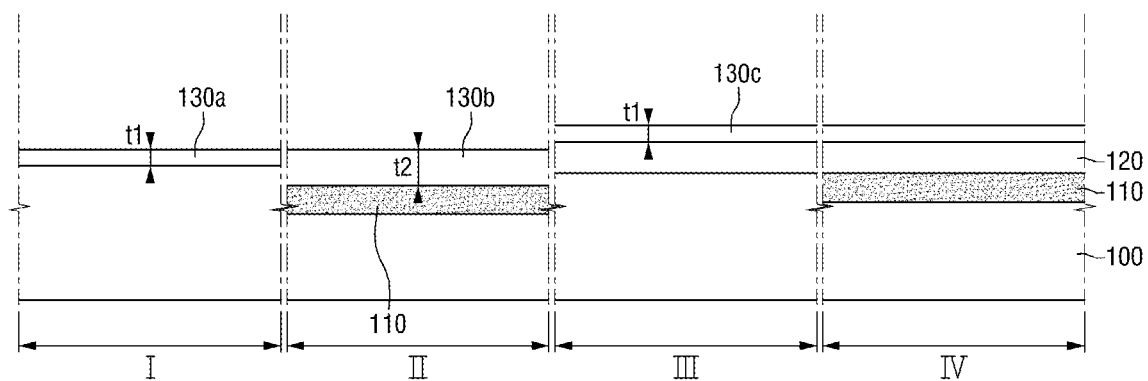


FIG. 6

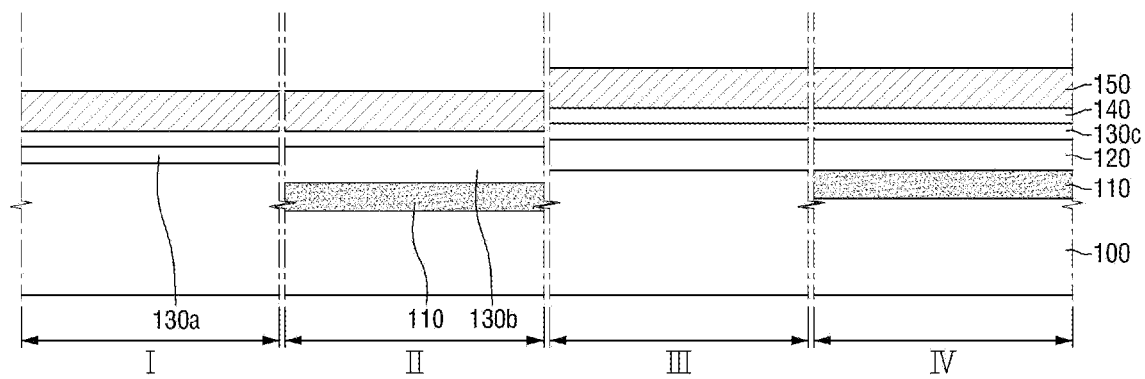


FIG. 7

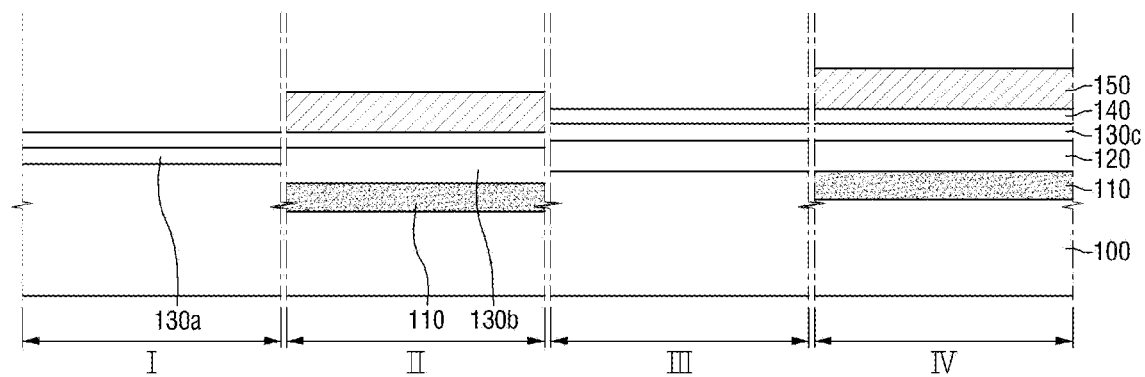


FIG. 8

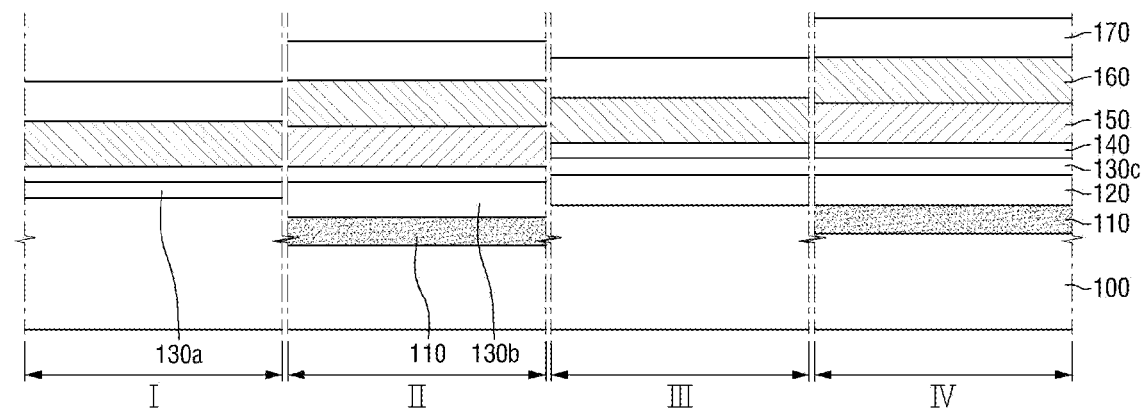


FIG. 9

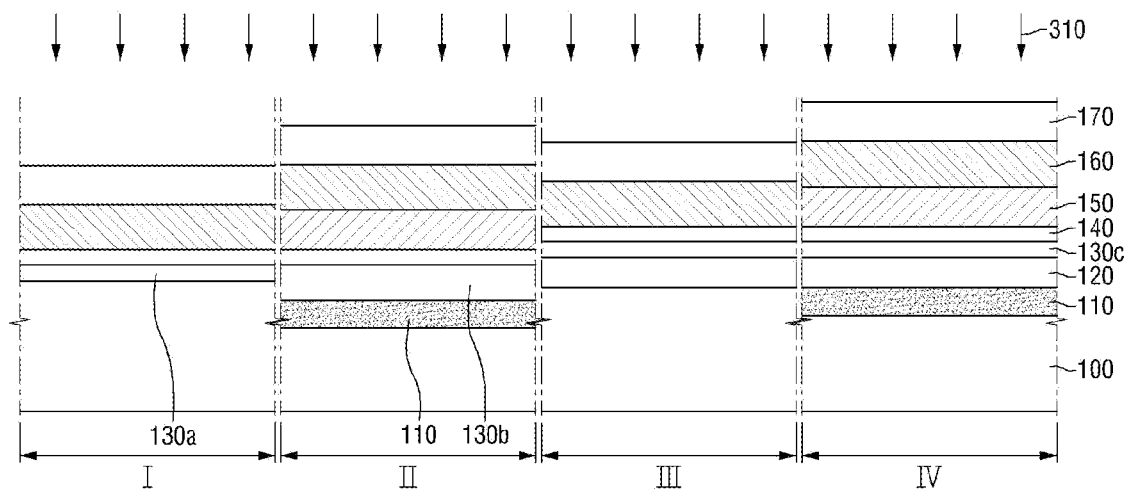


FIG. 10

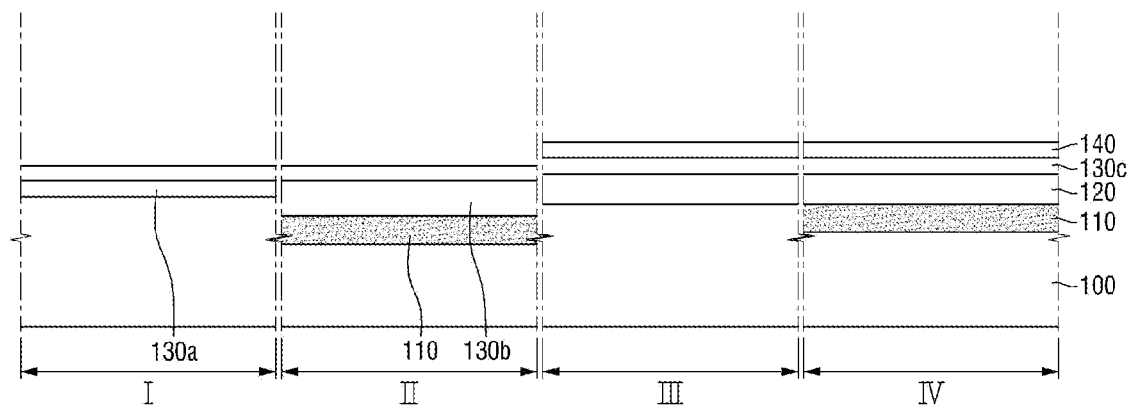


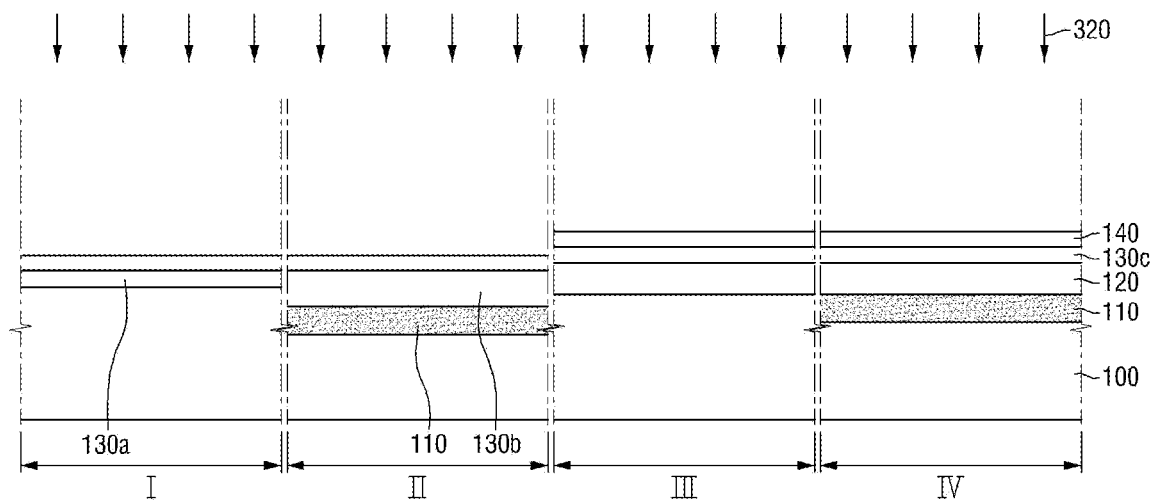
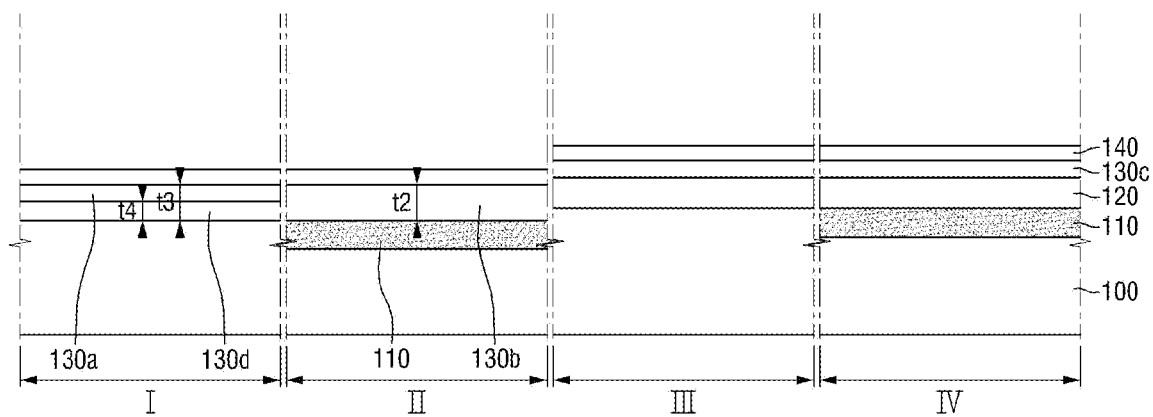
FIG. 11**FIG. 12**

FIG. 13

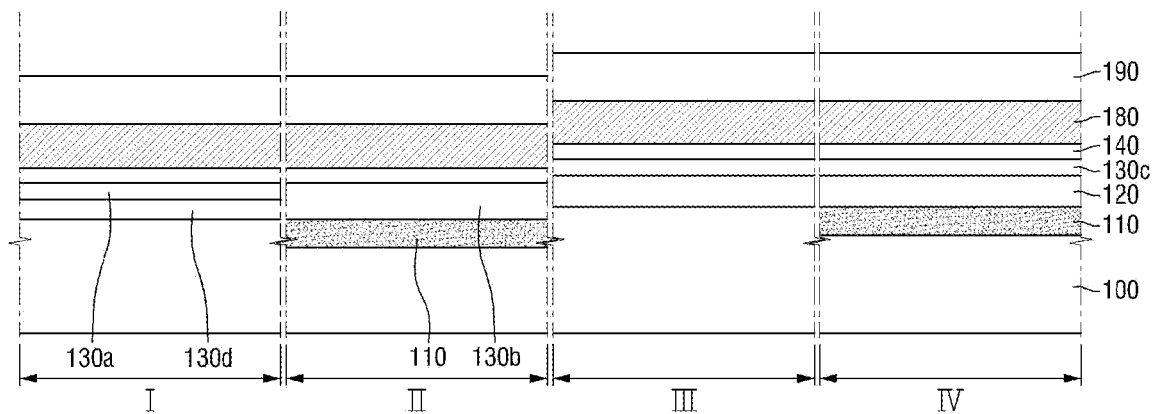


FIG. 14

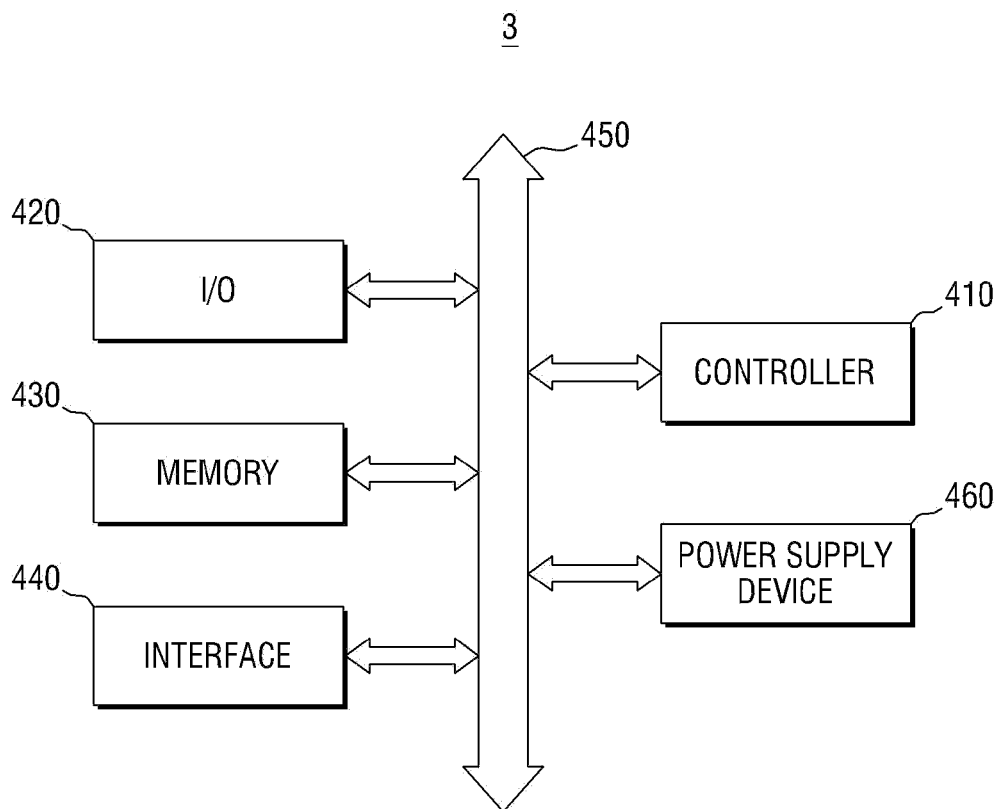


FIG. 15

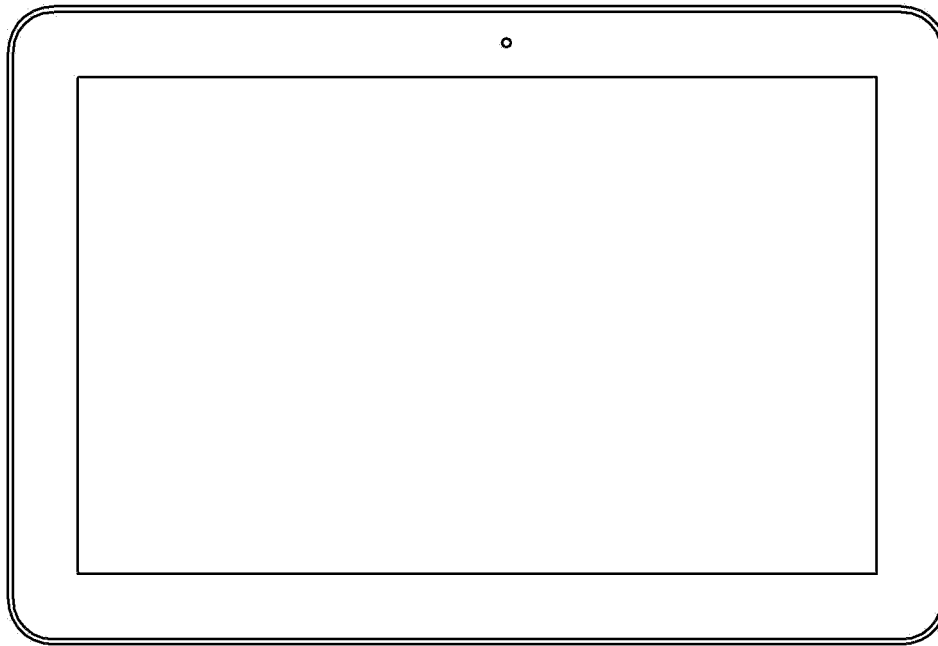
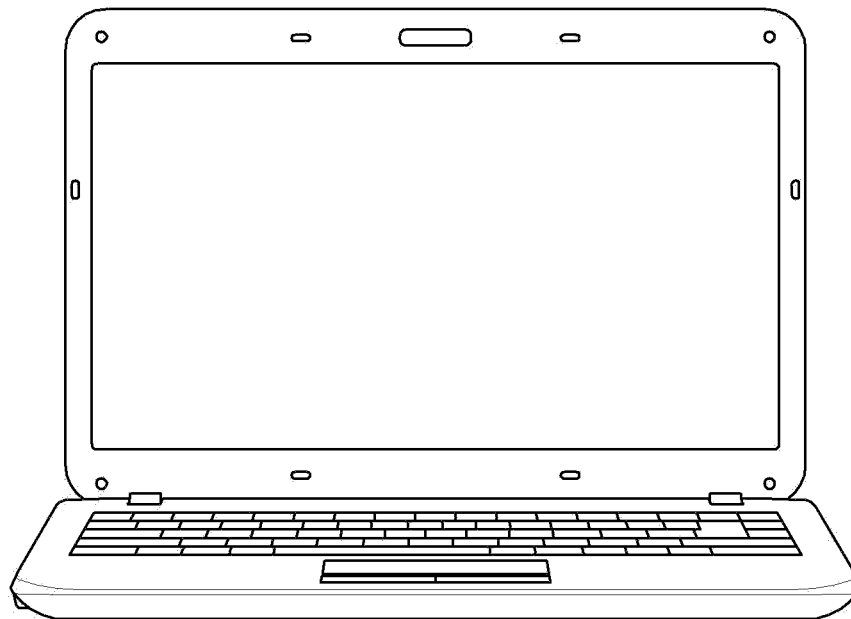


FIG. 16



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SEMICONDUCTOR DEVICE AND METHOD FOR FABRICATING THE SAME

CROSS-REFERENCE TO RELATED APPLICATIONS

This application is based on and claims priority from Korean Patent Application No. 10-2012-0099363, filed on Sep. 7, 2012, in the Korean Intellectual Property Office, the disclosure of which is incorporated herein in its entirety by reference.

BACKGROUND

1. Field

Some example embodiments relate to a semiconductor device and a method for fabricating the same.

2. Description of the Prior Art

A semiconductor device may be classified into a semiconductor storage device and a semiconductor logic device. The semiconductor logic device may be, for example, an integrated circuit which includes MOS transistors, diodes, and the like, and performs a logic operation or an arithmetic operation. In general, both an NMOS transistor and a PMOS transistor are used as the MOS transistors, and skew may occur in electrical characteristics between the NMOS transistor and the PMOS transistor.

SUMMARY

Some example embodiments provide a semiconductor device having improved electrical characteristics. Other example embodiments provide a method for fabricating a semiconductor device having improved electrical characteristics.

According to an example embodiment, a semiconductor device includes a first interface film on a first area of a substrate, the first interface film including a first growth interface film and a second growth interface film on a lower portion of the first growth interface film, a first dielectric film on the first interface film, and a first gate electrode on the first dielectric film.

According to another example embodiment, a method for fabricating a semiconductor device includes defining a first area and a second area on a substrate, growing an interface material layer on the substrate, forming a dielectric material layer on the interface material layer, forming a first work function control material layer on the dielectric material layer in the second area of the substrate, forming a second work function control material layer on the dielectric material layer and the first work function control material layer, annealing the first work function control material layer and the second work function control material layer, removing the annealed first and second work function control material layers, and forming a re-growth interface material layer on a lower portion of the interface material layer in the first area of the substrate by re-growing the interface material layer in a direction of the substrate using an oxygen plasma process.

According to another example embodiment, a structure includes at least one first interface film on a first area of a substrate, the at least one first interface film having a first thickness, and a second interface film on a second area of the substrate, the second interface film having a second thickness greater than the first thickness, wherein a top surface of the at least one first interface film is formed at a same level as the second interface film.

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According to another example embodiment, a semiconductor device includes a substrate including a first area and a second area, at least one interface film on the substrate, a first dielectric film on the at least one interface film in the first area of the substrate, the first dielectric film including lanthanum oxide (LaO), a second dielectric film on the at least one interface film in the second area of the substrate, the second dielectric film including aluminum oxide (AlO), and first and second gate electrodes on the first and second dielectric films, respectively.

Additional advantages and features of example embodiments will be set forth in part in the description which follows and in part will become apparent to those having ordinary skill in the art upon examination of the following or may be learned from practice of the example embodiments.

BRIEF DESCRIPTION OF THE DRAWINGS

The above and other features and advantages of example embodiments will be more apparent from the following detailed description taken in conjunction with the accompanying drawings, in which:

FIG. 1 is a schematic cross-sectional view of a semiconductor device according to an example embodiment;

FIG. 2 is a schematic cross-sectional view of a semiconductor device according to another example embodiment;

FIGS. 3 to 13 are cross-sectional views explaining intermediate steps of a method for fabricating the semiconductor device of FIG. 2;

FIG. 14 is a schematic block diagram of an electronic system including a semiconductor device according to some example embodiments; and

FIGS. 15 and 16 are example views of an electronic system to which the semiconductor device according to some example embodiments can be applied.

DETAILED DESCRIPTION OF THE EMBODIMENTS

The inventive concepts will now be described more fully hereinafter with reference to the accompanying drawings, in which example embodiments are shown. The inventive concepts may, however, be embodied in different forms and should not be construed as limited to the embodiments set forth herein. Rather, these embodiments are provided so that this disclosure will be thorough and complete, and will fully convey the scope of the inventive concepts to those skilled in the art. The same reference numbers indicate the same components throughout the specification. In the attached figures, the thickness of layers and regions is exaggerated for clarity.

It will also be understood that when a layer is referred to as being “on” another layer or substrate, it can be directly on the other layer or substrate, or intervening layers may also be present. In contrast, when an element is referred to as being “directly on” another element, there are no intervening elements present.

Spatially relative terms, such as “beneath,” “below,” “lower,” “above,” “upper” and the like, may be used herein for ease of description to describe one element or feature’s relationship to another element(s) or feature(s) as illustrated in the figures. It will be understood that the spatially relative terms are intended to encompass different orientations of the device in use or operation in addition to the orientation depicted in the figures. For example, if the device in the figures is turned over, elements described as “below” or “beneath” other elements or features would then be oriented “above” the other elements or features. Thus, the example

term “below” can encompass both an orientation of above and below. The device may be otherwise oriented (rotated 90 degrees or at other orientations) and the spatially relative descriptors used herein interpreted accordingly.

The use of the terms “a” and “an” and “the” and similar referents in the context of describing the inventive concepts (especially in the context of the following claims) are to be construed to cover both the singular and the plural, unless otherwise indicated herein or clearly contradicted by context. The terms “comprising,” “having,” “including,” and “containing” are to be construed as open-ended terms (i.e., meaning “including, but not limited to,”) unless otherwise noted.

Unless defined otherwise, all technical and scientific terms used herein have the same meaning as commonly understood by one of ordinary skill in the art to which the inventive concepts belong. It is noted that the use of any and all examples, or example terms provided herein is intended merely to better illuminate the inventive concepts and is not a limitation on the scope of the inventive concepts unless otherwise specified. Further, unless defined otherwise, all terms defined in generally used dictionaries may not be overly interpreted.

The inventive concepts will be described with reference to perspective views, cross-sectional views, and/or plan views, in which example embodiments are shown. Thus, the profile of an example view may be modified according to manufacturing techniques and/or allowances. That is, example embodiments are not intended to limit the scope of the inventive concepts but cover all changes and modifications that can be caused due to a change in manufacturing process. Thus, regions shown in the drawings are illustrated in schematic form and the shapes of the regions are presented simply by way of illustration and not as a limitation.

Hereinafter, with reference to FIG. 1, a semiconductor device according to an example embodiment will be described. FIG. 1 is a schematic cross-sectional view of a semiconductor device according to an example embodiment.

Referring to FIG. 1, on a substrate **100** of a semiconductor device **1** according to an example embodiment, a first area I and a second area II are defined.

The substrate **100** may be, for example, a rigid substrate, such as a substrate that is made of one or more semiconductor materials selected from the group consisting of Si, Ge, SiGe, GaP, GaAs, SiC, SiGeC, InAs, and InP, an SOI (Silicon On Insulator) substrate, a quartz substrate, or a glass substrate for display, or a flexible plastic substrate made of polyimide, PET (PolyEthylene Terephthalate), PEN (PolyEthylene Naphthalate), PMMA (PolyMethyl MethAcrylate), PC (PolyCarbonate), PES (PolyEtherSulfone), or polyester.

A first transistor **10** is formed in the first area I of the substrate **100**, and a second transistor **20** is formed in the second area II of the substrate **100**. Here, the first transistor **10** may be an NMOS transistor (n-channel MOSFET), and the second transistor **20** may be a PMOS transistor (p-channel MOSFET).

The first transistor **10** includes a first gate stack and first source/drain areas **201**. Here, the first gate stack includes first interface films **131a** and **131d**, a first dielectric, i.e., high-k, film **141**, first gate electrodes **191** and **181**, and the like.

The first interface films **131a** and **131d** are interposed between the substrate **100** and the first dielectric, i.e., high-k, film **141** to prevent or reduce an inferior interface between the substrate **100** and the first dielectric, i.e., high-k, film **141**. The first interface films **131a** and **131d** may be made of a low-k material having permittivity that is equal to or less than 9. The first interface films **131a** and **131d** may include, for example, a silicon oxynitride film. However, example embodiments are

not limited thereto, but the first interface films **131a** and **131d** may be made of, for example, a silicon oxide film or a silicate film, or a combination thereof.

The first interface films **131a** and **131d** may be formed as a structure in which a first growth interface film **131a** and a second growth interface film **131d** are laminated. The second growth interface film **131d** may be an interface film which is interposed between the substrate **100** and the first growth interface film **131a** and is re-grown from the first growth interface film **131a**. The first growth interface film **131a** is formed with a first thickness **t1**, and the second growth interface film **131d** is formed with a fourth thickness **t4**. The first thickness **t1** may be relatively thinner than a thickness **t2** of a second interface film **132b** to be described later.

The first dielectric, i.e., high-k, film **141** is formed on the first interface films **131a** and **131d**. The first dielectric, i.e., high-k, film **141** may be a high-k material layer. The first dielectric, i.e., high-k, film **141** may include, for example, a material selected from the group consisting of HfO₂, ZrO₂, Ta₂O₅, TiO₂, SrTiO₃, or (Ba, Sr)TiO₃. The first dielectric, i.e., high-k, film **141** may be formed with a proper thickness depending on the material that is included therein.

The first gate electrodes **181** and **191** are formed on the first dielectric, i.e., high-k, film **141**. The first gate electrodes **181** and **191** may be a laminate of a metal electrode and a silicon electrode, but are not limited thereto. The first metal electrode **181** may include, for example, TiN, and the first silicon electrode **191** may include, for example, amorphous silicon or poly silicon.

The first source/drain areas **201** are arranged on both sides of the first gate stack in the substrate **100**. An n-type impurity may be injected onto the first source/drain areas **201**. The n-type impurity may include, for example, indium (P), arsenic (As), antimony (Sb), bismuth (Bi), or the like. A channel area of the first transistor **10** may be formed between a pair of the first source/drain areas **201**.

The second transistor **20** includes a second gate stack and second source/drain areas **202**. Here, the second gate stack includes a second interface film **132b**, a second dielectric, i.e., high-k, film **142**, second gate electrodes **182** and **192**, and the like.

The second interface films **132b** is interposed between the substrate **100** and the second dielectric, i.e., high-k, film **142** to prevent or reduce an inferior interface between the substrate **100** and the second dielectric, i.e., high-k, film **142**. The second interface film **132b** may be a low-k material layer, and may include, for example, a silicon oxynitride film. However, example embodiments are not limited thereto, but the second interface film **132b** may be made of, for example, a silicon oxide film, a silicate film, or a combination thereof.

Unlike the first interface films **131a** and **131d**, the second interface film **132b** is formed as a single layer. The second interface film **132b** is formed with the second thickness **t2**.

As described above, the overall thickness **t3** of the first interface films **131a** and **131d** may be thinner than the second thickness **t2**, but is not limited thereto. The overall thickness **t3** may be variously controlled depending on the performance of the NMOS transistor **10** and the PMOS transistor **20**. The upper surface of the first interface films **131a** and **131d** is formed at the same level as the upper surface of the second interface film **132b**.

Accordingly, in the semiconductor device **1** according to an example embodiment, T_{inv} (inversion-layer thickness) of the NMOS transistor **10** is increased, and the T_{inv} skew between the NMOS transistor **10** and the PMOS transistor **20** is decreased. Further, without any change of T_{inv} of the PMOS transistor **20**, gate leakage current I_{gon} of the PMOS

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transistor **20** is decreased. Here, T_{inv} indicates an average position or centroid of inversion charge below the interface between the substrate and a gate insulating film in the transistor.

The second dielectric, i.e., high-k, film **142** is formed on the second interface film **132b**. The second dielectric, i.e., high-k, film **142** may be a high-k material layer **140** that is substantially the same as the first dielectric, i.e., high-k, film **141**. The second dielectric, i.e., high-k, film **142** may include, for example, a material selected from the group consisting of HfO_2 , $SrTiO_3$, or $(Ba, Sr)TiO_3$. The second dielectric, i.e., high-k, film **142** may be formed with a proper thickness depending on the material that is included therein.

The second gate electrodes **182** and **192** are formed on the second dielectric, i.e., high-k, film **142**. The second gate electrodes **182** and **192** may be a laminate of a metal electrode and a silicon electrode, which is substantially the same as the first gate electrodes, but are not limited thereto. The second metal electrode **182** may include, for example, TiN, and the second silicon electrode **192** may include, for example, amorphous silicon or poly silicon.

The second source/drain areas **202** are arranged on both sides of the second gate stack in the substrate **100**. A p-type impurity may be injected into the second source/drain areas **202**. The p-type impurity may include, for example, boron (B), aluminum (Al), indium (In), gallium (Ga), or the like. A channel area of the second transistor **20** may be formed between a pair of the second source/drain areas **202**.

A channel layer **110** may be arranged in the channel area of the second transistor **20** in the second area II of the substrate **100**. The channel layer **110** may include, for example, SiGe. The SiGe channel layer **110** may improve mobility of holes in the PMOS transistor. A Si cap layer (not shown) may be formed on an upper portion of the SiGe channel layer **110**, and a Si buffer layer (not shown) may be formed on a lower portion of the SiGe channel layer **110**.

Lanthanum oxide (LaO) may be included in the first dielectric, i.e., high-k, film **141** of the first transistor **10**, but LaO may not be included in the second dielectric, i.e., high-k, film **142** of the second transistor **20**. LaO serves to adjust the work function and the threshold voltage V_t of the first transistor **10**. Further, aluminum oxide (AlO) may be included in the second dielectric, i.e., high-k, film **142** of the second transistor **20**, but AlO may not be included in the first dielectric, i.e., high-k, film **141** of the first transistor **10**. AlO serves to adjust the work function and the threshold voltage V_t of the second transistor **20**. As a result, in the semiconductor device **1** according to an example embodiment, the operating characteristics of the first, i.e., NMOS, transistor **10** and the second, i.e., PMOS, transistor **20** may be improved.

Hereinafter, referring to FIG. **2**, a semiconductor device according to another example embodiment will be described. FIG. **2** is a schematic cross-sectional view of a semiconductor device according to another example embodiment. For convenience in explanation, the explanation will be made around the point of difference from FIG. **1**.

Referring to FIG. **2**, on a substrate **100** of a semiconductor device **2** according to another example embodiment, first to fourth areas I to IV are defined.

The substrate **100** may be, for example, a rigid substrate, such as a substrate that is made of one or more semiconductor materials selected from the group consisting of Si, Ge, SiGe, GaP, GaAs, SiC, SiGeC, InAs, and InP, an SOI (Silicon On Insulator) substrate, a quartz substrate, or a glass substrate for display, or a flexible plastic substrate made of polyimide, PET (PolyEthylene Terephthalate), PEN (PolyEthylene Naphtha-

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late), PMMA (PolyMethyl MethAcrylate), PC (PolyCarbonate), PES (PolyEtherSulfone), or polyester.

A first transistor **10** is formed in the first area I of the substrate **100**, a second transistor **20** is formed in the second area II of the substrate **100**, a third transistor **30** is formed in the third area III of the substrate **100**, and a fourth transistor **40** is formed in the fourth area IV of the substrate **100**. Here, the first transistor **10** and the third transistor **30** may be NMOS transistors (n-channel MOSFETs), and the second transistor **20** and the fourth transistor **40** may be PMOS transistors (p-channel MOSFETs).

The first transistor **10** and the second transistor **20** may be formed in substantially the same manner as the first transistor **10** and the second transistor **20** in FIG. **1**, and the detailed description thereof will be omitted hereinafter.

The third transistor **30** includes a third gate stack and third source/drain areas **203**. Here, the third gate stack includes a first insulating film **123**, a third interface films **133c**, a third dielectric, i.e., high-k, film **143**, third gate electrodes **183** and **193**, and the like.

The first insulating film **123** is formed in the third area III of the substrate **100**. The first insulating film **123** may include, for example, a silicon oxide film, but is not limited thereto. The first insulating film **123** is formed to be relatively thicker than the first to fourth interface films **134c**, **131a**, **131d**, **132b**, **133c**, and **134c**.

The third interface film **133c** is interposed between the first insulating film **123** and the third dielectric, i.e., high-k, film **143**. The third interface film **133c** may be made of a low-k material in substantially the same manner as the second interface film **132b**. The third interface film **133c** may include, for example, a silicon oxynitride film. However, example embodiments are not limited thereto, but the third interface film **133c** may be made of for example, a silicon oxide film, a silicate film, or a combination thereof. The third interface film **133c** may be formed as a single layer in substantially the same manner as the second interface film **132b**, and may be formed with substantially the same thickness t_1 as the first growth interface film **131a**.

The third dielectric, i.e., high-k, film **143** is formed on the third interface film **133c**. The third dielectric, i.e., high-k, film **143** may be a dielectric, i.e., high-k, material layer **140** in substantially the same manner as the first dielectric, i.e., high-k, film **141**. The third dielectric, i.e., high-k, film **143** may include, for example, a material selected from the group consisting of HfO_2 , ZrO_2 , Ta_2O_5 , TiO_2 , $SrTiO_3$, or $(Ba, Sr)TiO_3$. The third dielectric, i.e., high-k, film **143** may be formed with a proper thickness depending on the material that is included therein.

The third gate electrodes **183** and **193** are formed on the third dielectric, i.e., high-k, film **143**. The third gate electrodes **183** and **193** may be a laminate of a metal electrode and a silicon electrode in substantially the same manner as the first gate electrode, but are not limited thereto. The third metal electrode **183** may include, for example, TiN, and the third silicon electrode **193** may include, for example, amorphous silicon or poly silicon.

The third source/drain areas **123** are arranged on both sides of the third gate stack in the substrate **100**. An n-type impurity may be injected into the third source/drain areas **123**. The n-type impurity may include, for example, indium (P), arsenic (As), antimony (Sb), bismuth (Bi), or the like. A channel area of the third transistor **30** may be formed between a pair of the third source/drain areas **123**.

The fourth transistor **40** includes a fourth gate stack and fourth source/drain areas **204**. Here, the fourth gate stack includes a second insulating film **124**, a fourth interface film

134c, a fourth dielectric, i.e., high-k, film **144**, fourth gate electrodes **184** and **194**, and the like.

The second insulating film **124** is formed in the fourth area IV of the substrate **100**. The second insulating film **124** may include a silicon oxide film in substantially the same manner as the first insulating film **123**, but is not limited thereto. The second insulating film **124** is formed to be relatively thicker than the first to fourth interface films **131a**, **131d**, **132b**, **133c**, and **134c**.

The fourth interface film **134c** is interposed between the second insulating film **124** and the fourth dielectric, i.e., high-k, film **144**. The fourth interface film **134c** may be made of a low-k material in substantially the same manner as the second interface film **132b**, and may include, for example, a silicon oxynitride film. However, example embodiments are not limited thereto, but the fourth interface film **134c** may be made of, for example, a silicon oxide film, a silicate film, or a combination thereof. The fourth interface film **134c** may be formed as a single layer in substantially the same manner as the second interface film **132b**, and may be formed with substantially the same thickness U as the first growth interface film **131a**.

The fourth dielectric, i.e., high-k, film **144** is formed on the fourth interface films **134c**. The fourth dielectric, i.e., high-k, film **144** may be a high-k material layer in substantially the same manner as the first dielectric, i.e., high-k, film **141**. The fourth dielectric, i.e., high-k, film **144** may include, for example, a material selected from the group consisting of HfO_2 , ZrO_2 , Ta_2O_5 , TiO_2 , SrTiO_3 , or $(\text{Ba}, \text{Sr})\text{TiO}_3$. The fourth dielectric, i.e., high-k, film **144** may be formed with a proper thickness depending on the material that is included therein.

The fourth gate electrodes **184** and **194** are formed on the fourth dielectric, i.e., high-k, film **144**. The fourth gate electrodes **184** and **194** may be a laminate of a metal electrode and a silicon electrode in substantially the same manner as the first gate electrode, but are not limited thereto. The fourth metal electrode **184** may include, for example, TiN, and the fourth silicon electrode **194** may include, for example, amorphous silicon or poly silicon.

The fourth source/drain areas **204** are arranged on both sides of the fourth gate stack in the substrate **100**. A p-type impurity may be injected into the fourth source/drain areas **204**. The p-type impurity may include, for example, boron (B), aluminum (Al), indium (In), gallium (Ga), or the like. A channel area of the fourth transistor **40** may be formed between a pair of the fourth source/drain areas **204**.

A channel layer **110** may be arranged in the channel area of the fourth transistor **40** in the fourth area IV of the substrate **100**. The channel layer **110** may include, for example, SiGe. The SiGe channel layer **110** may improve mobility of holes in the PMOS transistor. A Si cap layer (not shown) may be formed on an upper portion of the SiGe channel layer **110**, and a Si buffer layer (not shown) may be formed on a lower portion of the SiGe channel layer **110**.

Lanthanum oxide (LaO) may be included in the third dielectric, i.e., high-k, film **143** of the third transistor **30**, but LaO may not be included in the fourth dielectric, i.e., high-k, film **144** of the fourth transistor **40**. LaO serves to adjust the work function and the threshold voltage V_t of the third, i.e., NMOS, transistor **30**. Further, aluminum oxide (AlO) may be included in the fourth dielectric, i.e., high-k, film **144** of the fourth transistor **40**, but AlO may not be included in the third dielectric, i.e., high-k, film **143** of the fourth, i.e., PMOS, transistor **40**. AlO serves to adjust the work function and the threshold voltage V_t of the PMOS transistor **40**. As a result, in the semiconductor device **2** according to another example

embodiment, the operating characteristics of the NMOS transistor **30** and the PMOS transistor **40** may be improved.

In the semiconductor device **2** according to another example embodiment, the first transistor **10** and the second transistor **20** may be SG transistors, and the third transistor **30** and the fourth transistor **40** may be EG transistors. Here, the SG transistor indicates a transistor for relatively low voltage having a relatively thin gate insulating film, and the EG transistor indicates a transistor for relatively high voltage having a relatively thick gate insulating film. Here, each of the first transistor **10** and the second transistor **20** has an interface film and a gate insulating film including a dielectric, i.e., high-k, film, and each of the third transistor **30** and the fourth transistor **40** has an insulating film, an interface film, and a gate insulating film including a dielectric, i.e., high-k, film. In the semiconductor logic device, the EG transistor may be used in, for example, an input/output module, and the SG transistor may be used in, for example, a logic module.

Hereinafter, referring to FIGS. **3** to **13**, a method for fabricating a semiconductor device according to an example embodiment will be described. FIGS. **3** to **13** are cross-sectional views explaining intermediate steps of a method for fabricating the semiconductor device of FIG. **2**. Since the method for fabricating a semiconductor device illustrated in FIG. **1** is apparent from the method for fabricating a semiconductor device according to an example embodiment to be described with reference to FIGS. **3** to **13**, the detailed description thereof will be omitted.

Referring to FIG. **3**, a substrate **100** is prepared. The substrate **100** may be a rigid substrate, such as a substrate that is made of one or more semiconductor materials selected from the group consisting of Si, Ge, SiGe, GaP, GaAs, SiC, SiGeC, InAs, and InP, an SOI substrate, a quartz substrate, or a glass substrate for display, or a flexible plastic substrate made of polyimide, PET, PEN, PMMA, PC, PES, or polyester.

A device isolation area (not illustrated) that defines an active area is formed on the substrate **100**. At this time, the device isolation area may be formed of STI (Shallow Trench Isolation) or FOX (Field Oxide). The device isolation area may define active areas of a first area I, a second area II, a third area III, and a fourth area IV on the substrate **100**.

Then, in order to improve mobility of holes, a channel layer **110** is formed in the second area II and the fourth area IV of the substrate **100**. The channel layer **110** may be formed to include, for example, SiGe.

Then, an insulating material layer **120** for forming an insulating film is formed on the substrate **100**. The insulating material layer **120** may be formed of, for example, a silicon oxide film, but is not limited thereto. At this time, the insulating material layer **120** is formed to be thicker than an interface material layer **130** to be described later. The insulating material layer **120** may be formed using, for example, CVD (Chemical Vapor Deposition), PECVD (Plasma Enhanced Chemical Vapor Deposition), or the like.

Referring to FIG. **4**, a first mask film (not illustrated) is formed on the insulating material layer **120**. The first mask film may include, for example, a silicon nitride film. A first mask pattern is formed by patterning the first mask film. At this time, the first and second areas I and II of the insulating material layer **120** are exposed by the first mask pattern. Then, an exposed area of the insulating material layer **120** is etched using the first mask pattern as an etching mask. Accordingly, the insulating material layer **120** is formed only on the third and fourth areas III and IV of the substrate **100**, but is not formed on the first and second areas I and II of the substrate **100**. An upper surface of the insulating material layer **120** is

exposed by removing the first mask pattern that remains on the insulating material layer **120**.

Referring to FIG. 5, interface material layers **130a**, **130b**, and **130c** for forming interface films on the first, second, and third areas I, II and III of the substrate **100** and the insulating material layer **120** are conformally grown. The interface material layers **130a**, **130b**, and **130c** may be formed of a silicon oxynitride film, a silicon oxide film, a silicate film, or a combination thereof. The interface material layers **130a**, **130b**, and **130c** are formed of a single layer. The interface material layer **130a** of the first area I is formed with a first thickness t_1 , and the interface material layer **130b** of the second area II is formed with a second thickness t_2 . Since the channel layer **110** is arranged in the second area II of the substrate **100**, the first thickness t_1 may be relatively thinner than the second thickness t_2 . Since the insulating material layer **120** is formed on the third and fourth areas III and IV of the substrate **100**, the interface material layer **130c** of the third and fourth areas III and IV may be formed with the thickness t_1 that is substantially the same as the thickness of the interface material layer **130a** of the first area I.

Referring to FIG. 6, a dielectric, i.e., high-k, material layer **140** for forming a dielectric, i.e., high-k, film on the interface material layers **130a**, **130b**, and **130c** is conformally formed. The dielectric material layer **140** may be formed of, for example, a material, which is a high-k material, selected from the group consisting of HfO_2 , ZrO_2 , Ta_2O_5 , TiO_2 , SrTiO_3 , or $(\text{Ba}, \text{Sr})\text{TiO}_3$. The dielectric, i.e., high-k, material layer **140** may be formed with a proper thickness depending on the selected material.

A first work function control material layer **150** is conformally formed on the dielectric, i.e., high-k, material layer **140**. The first work function control material layer **150** may include, for example, Al. More specifically, the first work function control material layer **150** may include a lower TiN film, an Al film, and an upper TiN film, which are sequentially laminated. Further, the first work function control material layer **150** may exclude the upper TiN film and include the Al film and the upper TiN film, which are sequentially laminated. The first work function control material is not limited to Al but may include, for example, at least one selected from the group consisting of Al, Ti, Zr, Hf, and Mg.

Referring to FIG. 7, a second mask film (not illustrated) is formed on the first work function control material layer **150**. The second mask film may include, for example, a silicon nitride film. A second mask pattern is formed by patterning the second mask film. First and third areas I and III of the first work function control material layer **150** are exposed by the second mask pattern. An exposed area of the first work function control material layer **150** is etched using the second mask pattern as an etching mask. Accordingly, the first work function control material layer **150** is formed only on the second and fourth areas II and IV of the substrate **100**, but is not formed on the first and third areas I and III of the substrate **100**.

An upper surface of the first work function control material layer **150** is exposed by removing the second mask pattern that remains on the first work function control material layer **150**.

Referring to FIG. 8, a second work function control material layer **160** is conformally formed on the dielectric, i.e., high-k, material layer **140** and the first work function control material layer **150**. The second work function control material layer **160** may include, for example, La. More specifically, the second work function control material layer **160** may include a La film, a TiN film, and a poly silicon film, which are sequentially laminated. The second work function

control material is not limited to La, but may include at least one of La, Ge, Y, Lu, Sr, and Mg.

A barrier layer **170** may be conformally formed on the second work function control material layer **160**. The barrier layer **170** may include, for example, amorphous silicon. The barrier layer **170** serves to prevent or reduce the first work function control material layer **150** and the second work function control material layer **160** from being oxidized in an annealing process **310** to be described later. On the other hand, according to circumstances, the annealing process **310** to be described later may be performed without forming the barrier layer **170** on the second work function control material layer **160**.

Referring to FIG. 9, the first work function control material and the second work function control material are diffused into the dielectric, i.e., high-k, material layer **140** by performing an annealing process **310**. More specifically, the first work function control material Al is diffused into the second area II and the fourth area IV of the dielectric, i.e., high-k, material layer **140**, and the second work function control material La is diffused into the first area I and the third area III of the dielectric, i.e., high-k, material layer **140**. Here, since La is unable to pass through the first work function control material layer **150**, La cannot be diffused into the second area II and the fourth area IV of the dielectric, i.e., high-k, material layer **140**. As a result, the first area I and the third area III of the dielectric, i.e., high-k, material layer **140** include LaO, and the second area II and the fourth area IV of the dielectric, i.e., high-k, material layer **140** include AlO.

Referring to FIG. 10, an upper surface of the dielectric, i.e., high-k, material layer **140** is exposed by removing the first work function control material layer **150**, the second work function control material layer **160**, and the barrier layer **170**, which remain on the dielectric, i.e., high-k, material layer **140**.

Referring to FIG. 11, the interface material layers **130a**, **130b**, and **130c** are re-grown in the direction of the substrate **100** by performing an oxygen plasma process **320**. The oxygen plasma process **320** may be performed at a temperature of about 25° C. to about 500° C. and at a pressure of about 0.01 Torr to about 10 Torr. The oxygen plasma process **320** may be performed using a process gas including at least one of O_2 , N_2O , Ar, and N_2 . At this time, the dielectric, i.e., high-k, material, into which the work function control material has been diffused, serves to stop the re-growth of the interface material layers **130a**, **130b**, and **130c**. Further, in the oxygen plasma process **320**, oxygen vacancy that may occur during a process of removing the first work function control material layer **150** and the second work function control material layer **160** can be recovered. Accordingly, in the semiconductor device according to some example embodiments, the threshold voltage V_t of the PMOS transistor is reduced, and thus the narrow width effect can be improved.

Referring to FIG. 12, a re-growth interface material layer **130d** is formed on lower portions of the interface material layers **130a**, **130b**, and **130c** according to the oxygen plasma process **320**. The re-growth interface material layer **130d** is formed relatively thickly on the lower portion of the interface material layer **130a** of the first area I that is relatively thin, and is formed relatively thinly on the lower portion of the interface material layer **130b** of the second area II that is relatively thick.

At this time, the re-growth interface material film **130d** may not be re-grown on the lower portion of the interface material layer **130b** of the second area II. Here, the re-growth is not performed means that the re-growth is performed with a thickness that is thin enough to be disregarded in process. For this, the oxygen plasma process **320** requires a relatively

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strong oxidization force and must be performed at a relatively low temperature. In substantially the same manner as the interface material layer **130b** of the second area II, the re-growth interface material layer **130d** is not re-grown even on the lower portion of the interface material layer **130c** of the third and fourth areas III and IV.

The re-growth interface material layer **130d** may be formed with a fourth thickness **t4**. The overall thickness **t3** of the interface material layers **130a** and **130d** of the first area I that includes the re-growth interface material layer **130d** may be thinner than the second thickness **t2**, but is not limited thereto. The overall thickness may be variously controlled depending on the performance of the NMOS transistor and the PMOS transistor.

Referring to FIG. **13**, a metal layer **180** for forming a metal electrode is conformally formed on the dielectric, i.e., high-k, material layer **140**. The metal layer **180** may be made of various materials, and for example, may include TiN. A silicon layer **190** for forming a silicon electrode is conformally formed on the metal layer **180**. The silicon layer **190** may include, for example, amorphous silicon or poly silicon.

Referring again to FIG. **2**, the silicon layer **190**, the metal layer **180**, the dielectric, i.e., high-k, material layer **140**, the interface material layers **130a**, **130b**, and **130c**, and the insulating material layer **120** are sequentially etched by performing an etching process. At this time, the etching process may use, for example, RIE (Reactive Ion Etching) process. Accordingly, first to fourth gate stacks are formed on the substrate **100**.

Here, source/drain areas **201** to **204** of the first to fourth transistors **10** to **40** are formed by injecting impurities onto the active area of the substrate **100**. At this time, the respective source/drain areas **201** to **204** may be formed by DDD (Double Diffused Drain) or LDD (Lightly Doped Drain).

FIG. **14** is a schematic block diagram of an electronic system including the semiconductor device according to some example embodiments.

Referring to FIG. **14**, an electronic system **3** may include a controller **410**, an input/output (I/O) device **420**, a memory **430**, an interface **450**, a bus **450** and a power supply device **460**. The controller **410**, the I/O device **420**, the memory **430**, the interface **440** and/or the power supply device **460** may be coupled to one another through the bus **450**. The bus **450** corresponds to paths through which data is transferred.

The controller **410** may include at least one of a microprocessor, a digital signal processor, a microcontroller, and logic elements that can perform similar functions. The I/O device **420** may include a keypad, a keyboard, and a display device. The memory **430** may store data and/or commands. The interface **440** may function to transfer the data to a communication network or receive the data from the communication network. For example, the interface **440** may include an antenna or a wire/wireless transceiver. Although not illustrated, the electronic system **3** may further include a high-speed DRAM and/or SRAM as an operating memory for improving the operation of the controller **410**.

The semiconductor device according to some example embodiments may be provided inside the memory **430** or may be provided to a part of the controller **410** and the I/O device **420**.

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The electronic system **3** may be applied to a PDA (Personal Digital Assistant), a portable computer, a web tablet, a wireless phone, a mobile phone, a digital music player, a memory card, or all electronic devices that can transmit and/or receive information in wireless environments.

FIGS. **15** and **16** are example views of an electronic system to which the semiconductor device according to some example embodiments can be applied. FIG. **15** illustrates a tablet PC, and FIG. **16** illustrates a notebook PC. It is apparent to those of skilled in the art that the semiconductor device according to some example embodiments can be applied even to other integrated circuit devices that have not been illustrated.

In concluding the detailed description, those skilled in the art will appreciate that many variations and modifications can be made to the example embodiments without substantially departing from the principles of the inventive concepts. Therefore, the disclosed example embodiments are used in a generic and descriptive sense only and not for purposes of limitation.

What is claimed is:

1. A semiconductor device comprising:

a first interface film on a first area of a substrate, the first interface film including,
a first growth interface film, and
a second growth interface film on a lower portion of the first growth interface film;

a first dielectric film on the first interface film;
a first gate electrode on the first dielectric film; and
a second interface film on a second area of the substrate, the first growth interface film having a first thickness and the second interface film having a second thickness greater than the first thickness, and
the second interface film being in the form of a single layer.

2. The semiconductor device of claim 1, wherein the first growth interface film and the second growth interface film include at least one of silicon oxide and silicon oxynitride.

3. The semiconductor device of claim 1, further comprising:

a second dielectric film on the second interface film; and
a second gate electrode on the second dielectric film.

4. The semiconductor device of claim 3, wherein the first interface film has a third thickness less than the second thickness of the second interface film.

5. The semiconductor device of claim 3, further comprising:

a SiGe layer on a lower portion of the second interface film in the substrate.

6. The semiconductor device of claim 3, wherein the first interface film and the second interface film include at least one of silicon oxide and silicon oxynitride.

7. The semiconductor device of claim 1, wherein a dielectric constant of the first dielectric film is greater than a dielectric constant of the first and second growth interface films.

8. The semiconductor device of claim 1, wherein an upper surface of the first interface film is at a same level as an upper surface of the second interface film.

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